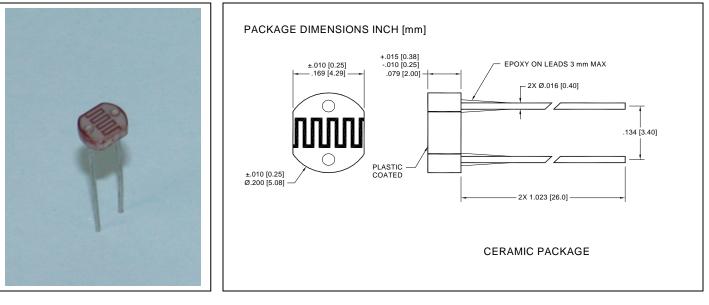


CdS Photoconductive Photocells



FEATURES

· Low cost

Visible light response

Sintered construction

DESCRIPTION

The **PDV-P8101** are (CdS), Photoconductive photocells designed to sense light from 400 to 700 nm. These light dependent resistors are available in a wide range of resistance values. They're packaged in a two leaded plastic-coated ceramic header.

APPLICATIONS

- Camera exposure
- Shutter controls
- Night light Controls

1000

100

10

1 +

Resistance in Kohms

CELL RESISTANCE VS. ILLUMINANCE

10

Illuminance in lux

100



SYMBOL	PARAMETER	MIN	MAX	UNITS	
V _{pk}	Applied Voltage		150	V	
P _{d Apo/At}	Continuous Power Dissipation		100	mW/°C	
To	Operating and Storage Temperature	-30	+75	°C	
Ts	Soldering Temperature*		+260	°C	

* 0.200 inch from base for 3 seconds with heat sink.

ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _D	Dark Resistance	After 10 sec. @ 10 Lux @ 2856 °K	0.15			ΜΩ
Rı	Illuminated Resistance	10 Lux @ 2856 °K	4		11	ΚΩ
S	Sensitivity	LOG(R100)-LOG(R10)** LOG(E100)-LOG(E10)***		0.65		Ω/Lux
λ range	Spectral Application Range	Flooded	400		700	nm
λ peak	Spectral Application Range	Flooded		520		nm
t _r	Rise Time	10 Lux @ 2856 °K		55		ms
T _f	Fall Time	After 10 Lux @ 2856 °K		20		ms

**R100, R10: cell resistances at 100 Lux and 10 Lux at 2856 °K respectively .

***E100, E10: luminances at 100 Lux and 10 Lux 2856 °K respectively.

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.